	Hits	Search Text	DBs
1	35	(((bit near6 line near6 contact) or (bit$3line near6 contact)) same DRAM) and ((substrate or wafer or workpiece) same ((dielectric or BPSG) near26 (deposit$4 or layer or coat$4 or film or form$3)) same (pattern$4 or mask) same (photoresist or resist or polyimide) same (etch$4 or RIE)) and ((photoresist or resist or photosensitive) same (pattern or mask) same develop$4 same (expos$4 or irradiat$4 or illuminate or photolithograph$4)) and ((fill$4 or deposit$4 or coat$4) same (window or opening or (bit$3line near6 contact near4 window) or (aspect near6 ratio) or (contact near9 hole)) same (conductive or metal$4 or polysilicon or polySi or tungsten or ("W" near3 plug)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
2	36	(((bit near6 line near6 contact) or (bit$3line near6 contact)) same DRAM) and ((substrate or wafer or workpiece) same ((dielectric or BPSG) near26 (deposit$4 or layer or coat$4 or film or form$3)) same (photoresist or resist or polyimide or (silicon near6 nitride) or (hard near9 mask)) same (etch$4 or RIE)) and ((photoresist or resist or photosensitive) same (pattern or mask) same develop$4 same (expos$4 or irradiat$4 or illuminate or photolithograph$4)) and ((fill$4 or deposit$4 or coat$4) same (window or opening or (bit$3line near6 contact near4 window) or (aspect near6 ratio) or (contact near9 hole)) same (conductive or metal$4 or polysilicon or polySi or tungsten or ("W" near3 plug)) same (planarization or planari$5 or CMP))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
3	263	(((bit near6 line near6 contact) or (bit$3line near6 contact)) same DRAM) and ((substrate or wafer or workpiece) same ((dielectric or BPSG) near26 (deposit$4 or layer or coat$4 or film or form$3)) same (photoresist or resist or polyimide or (silicon near6 nitride) or (hard near9 mask)) same (etch$4 or RIE)) and ((fill$4 or deposit$4 or coat$4) same (window or opening or (bit$3line near6 contact near4 window) or ‑ (aspect near6 ratio) or (contact near9 hole)) same (conductive or metal$4 or polysilicon or polySi or tungsten or ("W" near3 plug)) same (planarization or planari$5 or CMP))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
4	19	S4 and ((isolation or TEOS) same (layer or deposit$4 or coat$4 or film or form$3) same ((open$4 or hole or window) near16 (dielectric or BPSG)) same ((conductive or polysilicon or polySi or "W" or tungsten) near12 (form$3 or fill$4 or coat$4 or deposit$4)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
5	23	(((bit near6 line near6 contact) or (bit$3line near6 contact)) same DRAM) and ((substrate or wafer or workpiece) same ((dielectric or BPSG) near26 (deposit$4 or layer or coat$4 or film or form$3)) same ((control or electrode) near9 gate) same (photoresist or resist or polyimide or (silicon near6 nitride) or (hard near9 mask)) same (etch$4 or RIE)) and ((fill$4 or deposit$4 or coat$4) same (window or opening or (bit$3line near6 contact near4 window) or (aspect near6 ratio) or (contact near9 hole)) same (conductive or metal$4 or polysilicon or polySi or tungsten or ("W" near3 plug))) and ((isolation or TEOS) same (layer or deposit$4 or coat$4 or film or form$3) same ((open$4 or hole or window) near16 (dielectric or BPSG))) and (planariz$6 or CMP or (chemical near6 mechanical near6 polish$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
6	3	(("20050026409") or ("6696355") or ("5795823")).PN.	US-PGPUB; USPAT

	Hits	Search Text	DBs
7	36	(((bit near6 line near6 contact) or (bit$3line near6 contact)) same DRAM) and ((substrate or wafer or workpiece) same ((dielectric or BPSG) near26 (deposit$4 or layer or coat$4 or film or form$3)) same (photoresist or resist or polyimide or (silicon near6 nitride)) same (etch$4 or RIE)) and ((photoresist or resist or photosensitive) same (pattern or mask) same develop$4 same (expos$4 or irradiat$4 or illuminate or photolithograph$4)) and ((fill$4 or deposit$4 or coat$4) same (window or opening or (bit$3line near6 contact near4 window) or (aspect near6 ratio) or (contact near9 hole)) same (conductive or metal$4 or polysilicon or polySi or tungsten or ("W" near3 plug)) same (planarization or planari$5 or CMP))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB